Demonstration of room-temperature continuous-wave operation of InGaAs/AlGaAs quantum well lasers directly grown on on-axis silicon (001)

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Abstract

Room-temperature continuous-wave operation of InGaAs/AlGaAs quantum well lasers directly grown on on-axis silicon (001) has been demonstrated. A 420nm thick GaAs epilayer completely free of antiphase domains was initially grown on the silicon substrate in a metal-organic chemical vapor deposition system and the other epilayers including four sets of five-period strained-layer superlattices and the laser-structural layers were successively grown in a molecular beam epitaxy system. The lasers were prepared as broad-stripe Fabry-Perot ones with a stripe width of 21.5 μm and a cavity length of 1 mm. Typically, the threshold current and the corresponding threshold current density are 186.4 mA and 867 A/cm², respectively. The lasing wavelength is around 980 nm and the slope efficiency is 0.097 W/A with a single-facet output power of 22.5 mW at an injection current of 400 mA. This advancement makes the silicon-based monolithic optoelectronic integration relevant to quantum well lasers more promising with an enhanced feasibility.

Introduction

The exponential increase in the size of the internet protocol networks and the urgent demands in information interaction has become a hot issue, both in technology and economy. Photonic integrated circuits (PICs) integrated on silicon platforms, as a promising way to break through the limit of the conventional electrical interconnects, have attracted intense research.1,2 However, silicon-based on-chip light sources are still not commercialized due to the indirect bandgap of Si.3 Currently, monolithic III-V semiconductor laser diodes (LDs) fabricated on Si substrates are moving forward by both wafer bonding and heteroepitaxy, but the future requirements for lower power consumption.
and higher capacity may tilt the balance to the latter. In the heteroepitaxy process, material incompatibility between Si and III-V semiconductors will induce high-density crystal defects including threading dislocations (TDs), antiphase domains (APDs) and microcracks attributed to the different crystal structures and thermal expansion coefficients. These defects serve as non-radiation centers in active regions, providing a leakage path for carriers, and consequently yield the degradation of optoelectronic devices. For these reasons, decades of research have been devoted to solving these challenges. To decrease the threading dislocation density (TDD), various methods like insertion of dislocation filter layers (DFLs), thermal cycle annealing (TCA), post-growth annealing (PGA), aspect ratio trapping (ART) technology and Ge/GeSi multi-layers were applied. For the second hurdle, improvements including high-temperature thermal-annealing on Si substrates or taking V-grooved patterned Si substrates can exhibit diatomic steps on Si (001) surfaces and consequently suppress the formation of APDs. On the other part, the APDs can be eliminated via self-annihilation by depositing annealed Si buffers or AlGaAs seed layers. And the third challenge can be handled by limiting the whole thickness of device structures or using hollow-structure Si (001) substrates.

It is well known that the performance of quantum well (QW) lasers depends on the crystalline quality of GaAs buffers on Si substrates because QWs are more sensitive to temperatures and defects than quantum dots (QDs). Thus, great efforts have been made to reduce the nonradiative loss in the active regions of QW lasers. In our previous work, we reported an InGaAs/AlGaAs QW laser grown on a 4° offcut Si (001) substrate, operating under a room-temperature pulsed condition, demonstrating an extremely low threshold current density of 313 A/cm². However, the misoriented Si substrate is not compatible with the complementary metal-oxide-semiconductor (CMOS) technology. In 2014, Huang et al. adopted CMOS-compatible GaP/Si (001) substrates for InGaAs/GaAs quantum well lasers, but the properties of the lasers were restricted by the high-density TDD that led to the threshold current densities of 5.6 kA/cm² under a room-temperature pulsed condition. A similar work was reported in 2016, Aleshkin et al. deposited a Ge buffer on a planar Si (001) wafer before GaAs epilayers were grown, and finally, they obtained a room-temperature pulsed QW laser with the threshold current density of 5.5 kA/cm². In 2019, Shi et al. achieved an electrically pumped InGaAsP multiple QW laser diode fabricated on a nano-patterned V-grooved Si (001) substrate with a room-temperature continuous-wave (CW) lasing threshold current density of 2.05 kA/cm² and a maximum output power of 18 mW per facet. Such patterned Si (001) substrates increase the complexity of the substrate manufacturing process.

In this work, by leveraging CMOS-compatible Si (001) substrates along with defect-reduced growth methods, we demonstrate the room-temperature continuous-wave operation of InGaAs/AlGaAs QW lasers directly grown on on-axis silicon (001). The Si-based laser operates at room temperature with a CW lasing at 980.8 nm. The threshold current and the corresponding threshold current density are 186.4 mA and 867 A/cm², respectively. The single-facet output power of 22.5 mW is achieved at an injection current.
of 400 mA and the slope efficiency is 0.097 W/A.

**Growth and fabrication**

The whole epitaxial structure of InGaAs/AlGaAs QW lasers directly grown on on-axis Si (001) was shown in Fig. 1(a). For the initial 420 nm GaAs epilayer on Si (001), it was carried out in an Aixtron-CCS MOCVD system with the III-V precursors of high-purity trimethylgallium (TMGa) and arsine (AsH₃). All the Si substrates were 2-inch planar on-axis Si (001) substrates with offcut angles within ±0.5°. Before loading the substrates into the growth chamber, RCA chemical cleaning was performed to remove the residual contaminants. A surface hydrogen-annealing pretreatment on Si substrates in the growth chamber was applied to suppress the APDs generated in the epitaxy process of GaAs/Si (001) templates. The details of the growth procedure in MOCVD were reported in our previous work.²¹,²⁷ The surface morphology of 420 nm GaAs/Si (001) templates was measured by atomic force microscopy (AFM), as shown in Fig. 1(b). No APDs pattern was observed on the surface, and the root-mean-square (RMS) roughness was 0.96 nm under the measurement size of 10 μm × 10 μm.

The rest epitaxial structures were grown in a solid-source DCA-P600 MBE system. We first annealed the GaAs/Si (001) templates at 695°C (measured by a thermocouple) for deoxidation, following a 300 nm GaAs buffer to flatten the surface. Subsequently, four sets of strained-layer superlattices (SLSs) were grown as DFLs to further improve the material quality. Each SLS consisted of five periods of 10 nm In₀.₁₆₆Ga₀.₈₃₄As/10 nm GaAs, separated by 300 nm GaAs spacing layers. In the MBE system, the thickness required for significant plastic relaxation is 100 nm, much larger than the theoretical Mathew-Blakeslee critical thickness of 9 nm,²⁸ according with the designed thickness of one set of SLSs in this work. The growth of SLSs was terminated by shutting the Ga beam after the manipulator increased to 675°C. The dislocation density is reduced to below 10⁷/cm² after the 4th DFL, estimated by the cross-sectional bright-field scanning transmission electron microscopy (TEM) image,²⁰ as shown in Fig. 1(c). Then an 800 nm n-type GaAs contact layer was grown with a Si-doped concentration of 10¹⁸/cm³. Above the contact layer, a ~8 nm InGaAs QW was sandwiched by unintentional doped (UID) Al₀.₂Ga₀.₈As waveguide layers, surrounded by 1.5 μm Si-doped Al₀.₄Ga₀.₆As lower cladding layer and the same thickness of Be-doped Al₀.₄Ga₀.₆As upper cladding layer. At last, a 200 nm p-type GaAs contact layer was grown at the top of the structure. For comparison, the same laser structure on N-type GaAs substrates were also fabricated.
Fig. 1 (a) Schematic of the QW laser directly grown on on-axis Si (001) substrates. (b) AFM image of 420 nm GaAs grown on Si substrates in MOCVD with an RMS roughness of 0.96 nm, the scan area is 10×10 μm². (c) Cross-sectional bright-field TEM image of the whole buffer layers. Four stacks of 5-period InGaAs/GaAs SLSs as DFLs were grown in MBE.

The schematic of the fabricated laser structure and the cross-sectional scanning electron microscopy (SEM) image of the Si-based QW laser are shown in Fig. 2. The on-chip stripes were made into F-P lasers with 21.5×1000 μm² cavities. Ti/Pt/Au was used as the p-contact metal and AuGe/Ni/Au was used as the n-contact metal. The mirror-like facet, attributing a lower cavity loss, was processed by cleaving without any optical coating. Then as-cleaved laser chips were mounted onto Cu heatsinks with C-mount packages and the following tests were carried out under pulsed and CW conditions at room temperature.
Results and discussion

As shown in Fig. 3(a), typical light-current-voltage (L-I-V) properties of broad-stripe GaAs- and Si-based InGaAs/AlGaAs QW lasers were measured at room temperature (25°C) under a pulsed condition (50 μs-pulsed width, 5%-duty cycle). For the laser on the native substrate, the threshold current is 70.5 mA with the corresponding threshold current density of 328 A/cm². Under the same pulsed condition, the measured threshold current of the laser on the Si substrate is 165.1 mA and the threshold current density is 768 A/cm². Comparing the Si-based laser with the GaAs-based one, the threshold current density of the former is approximately two times as large as that of the latter, but it is still lower than the values of QW lasers fabricated on on-axis Si (001) substrates in previous reports.\textsuperscript{23,24} From the I-V curves, the differential resistance of the laser on the native substrate is 3.75 Ω, which is 42.8% of 8.76 Ω on the Si substrate. This discrepancy, on the one hand, may cause by the long lateral current path, which introduces a larger series resistance in the n-GaAs contact layer. On the other hand, the residual defects in active regions, even though have been filtered by thick buffers with four sets of DFLs, will still produce high leakage current and consequently lead to a larger value of series resistance.\textsuperscript{29} In addition, the slope efficiency is 0.113 W/A for the Si-based laser, and the single-facet output power of 15.5 mW is achieved at an injection current of 300 mA with no sign of power attenuation.

The aforementioned Si-based laser with a 21.5×1000 μm² cavity was tested under a CW condition at room temperature (25°C), as shown in Fig. 3(b). The threshold current is 186.4 mA, corresponding to a threshold current density of 867 A/cm². The maximum output power of 22.5 mW is obtained at 400 mA, and the slope efficiency is 0.097 W/A. It is distinguishing that the performance of Si-based laser measured under a CW condition is poorer than that carried out under a pulsed condition. This phenomenon can be illustrated by the self-accumulated heat in the device when operating at a CW injection current. The lasing spectrum of the Si-based laser under a CW condition is also presented in Fig. 3(b). When the injection current is 300 mA, the center wavelength of the spectrum is 980.8 nm.
Fig. 3 (a) Typical L-I-V properties of edge-emitting lasers on GaAs and Si substrates, respectively. The curves were measured under a pulsed condition at room temperature (25°C). (b) Performance of the Si-based laser measured under a CW condition at room temperature (25°C). The threshold current ($I_{th}$) is 186.4 mA and the slope efficiency ($E_s$) is 0.097 W/A. The inset presents the emission spectrum when the injection current is 300 mA.

**Conclusion**

In conclusion, we have demonstrated continuous-wave electrically pumped 980 nm InGaAs/AlGaAs quantum well lasers directly grown on planar on-axis Si (001). By using surface hydrogen-annealing technology in an MOCVD system, we obtained APD-free GaAs/Si (001) templates with a low surface roughness of 0.96 nm (10×10 μm²). Based on these GaAs/Si (001) templates, we completed the rest laser structures including GaAs buffers with DFLs in MBE. The F-P laser with 21.5-μm stripe width and 1-mm cavity length exhibited a pulsed emission at room temperature with the threshold current of 165.1 mA. The same device operated under a CW condition at room temperature was also measured. The threshold current is 186.4 mA with the corresponding threshold current density of 867 A/cm², the single-facet output power of 22.5 mW can be achieved at an injection current of 400 mA, and the slope efficiency is 0.097 W/A. This progress indicates the possibility of silicon-based QW lasers being applied into commercial products, which will promote further research on the monolithic integration of III-V semiconductor lasers on silicon via heteroepitaxial growth.

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